Ti–O Hybridization Effect of Lightly La-doped SrTiO₃ Observed by Resonant-Photoemission Spectroscopy

Tohru HIGUCHI, Takeyo TSUKAMOTO, Shu YAMAGUCHI¹, Yasuhisa TEZUKA² and Shik SHIN^{3,4}

Department of Applied Physics, Tokyo University of Science, 1-3 Kagurazaka, Shinjuku, Tokyo 162-8601, Japan

¹Department of Materials Science and Engineering, Nagoya Institute of Technology, Nagoya 466-8555, Japan

²Faculty of Science and Engineering, Hirosaki University, 1 Bunkyo-cho, Hirosaki 036-8561, Japan

³Institute for Solid State Physics, University of Tokyo, 5-1-5 Kashiwanoha, Kashiwa, Chiba 277-8581, Japan

⁴RIKEN, Sayo-gun, Hyogo 679-5148, Japan

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The electronic structure of lightly La-doped SrTiO₃ (La_xSr_{1-x}TiO₃) has been investigated by resonant-photoemission spectroscopy (RPES). The RPES spectra show that the Ti 3*d* partial density of states in the valence band decreases with increasing La dopant concentration. This finding indicates that the hybridization effect between the Ti 3*d* and O 2*p* states decreases with La³⁺ dopant concentration. [DOI: 10.1143/JJAP.41.5674]

KEYWORDS: La_xSr_{1-x}TiO₃, RPES, valence band, Ti–O hybridization effect, PDOS lattice parameter

Perovskite-type oxide SrTiO₃ exhibits *n*-type conductivity with Nb^{5+} substitution at the Ti^{4+} site and it becomes a superconductor at $T_c = 0.3 \text{ K.}^{1,2)}$ Nb-doped SrTiO₃ $(SrTi_{1-x}Nb_xO_3)$ is used as a substrate for the thin film deposition of ferroelectrics and superconductors because of their similar crystal structures and good lattice matching. Such doping can also be achieved by altering either of the two sublattices Sr^{2+} and O^{2-} . In particular, La^{3+} substitution at the Sr^{2+} site (La_xSr_{1-x}TiO₃) has been extensively studied because this system shows the insulator-to-metal transition as well as superconductivity.^{3–5)} In the small dopant region, the electrical conductivity of $La_x Sr_{1-x} TiO_3$ resembles with that of $SrTi_{1-x}Nb_xO_3$.²⁾ For this reason, $La_xSr_{1-x}TiO_3$ might also be used as a substrate for thin film deposition. Therefore, understanding the electronic structure of $La_xSr_{1-x}TiO_3$ ($x \le 0.05$) is also important in terms of the science and technology of materials.

The electronic structure of SrTiO₃ has been extensively studied over many years.⁶⁻¹⁶ The electronic structure can be explained from the energy band picture since there are only a few 3d electrons that bring about an appreciable correlation effect. It is well known that the valence band mainly consists of the O 2p state which strongly hybridizes with Ti 3d states, and the conduction band is formed by the Ti 3d states. This leads to a situation in which nonvanishing 3d electrons exist in the ground state. In the resonant-photoemission (RPES) study on $SrTi_{1-x}Nb_xO_3$, it was reported that the Ti 3d partial density of states (PDOS) in the valence band increases with increasing Nb⁵⁺ dopant concentration.^{11,16)} This result implies that the hybridization effect between the Ti 3d state and the O 2p state becomes more extensive with increasing Nb⁵⁺ dopant concentration, indicating the change of the effective charges of Ti⁴⁺ and O²⁻. Such a situation might also be expected in small doping region (x < 0.05) of $La_xSr_{1-x}TiO_3$.

In this study, the hybridization effect of $La_x Sr_{1-x} TiO_3$ (x = 0.01 and 0.05) has been investigated by RPES. We discuss how the hybridization effect is related to the lattice parameter of $La_x Sr_{1-x} TiO_3$.

Single crystals of $La_xSr_{1-x}TiO_3$ were synthesized by melt-quenching stoichiometric mixtures of La_2O_3 , TiO_2 , and SrO powders in a floating-zone furnace. The dopant concentrations were x = 0.01, 0.05. The crystals were examined by X-ray diffraction. RPES measurements were carried out at the revolving undulator beamline BL-19B at the Photon Factory (PF) of the High Energy Accelerator Organization (KEK), Tsukuba, Japan. Photoelectron energies were measured with an electrostatic hemispherical analyzer with a radius of 100 mm. The total energy resolution was approximately 40 meV. The samples were scraped *in situ* with a diamond file in a vacuum of 2.0×10^{-10} Torr in order to obtain a clean surface.

Figure 1(a) shows the constant final state (CFS) spectrum of $La_{0.05}Sr_{0.95}TiO_3$ measured at the kinetic energy where the secondary electron has a maximum intensity. This spectrum is regarded as the approximate absorption spectrum of Ti $3p \rightarrow 3d$. The CFS spectrum shows a broad maximum at approximately 47 eV.

Figure 1(b) shows the RPES spectra in the valence band region of $La_{0.05}Sr_{0.95}TiO_3$ measured at various photon energies. The valence band has two features, indicated by



Fig. 1. (a) CFS spectrum of $La_{0.05}Sr_{0.95}TiO_3$, corresponding to the Ti $3p \rightarrow 3d$ absorption spectrum. The numbers indicate the photon energies at which the RPES spectra were measured. (b) RPES spectra in the valence band region of $La_{0.05}Sr_{0.95}TiO_3$ excited at various photon energies.

A and B, which mainly consist of O 2p states mixed with Ti 3d states. It is well known that feature A and corresponds to the nonbonding state and feature B corresponds to the bonding state which is well mixed with Ti 3d states. The intensity of the bonding state is enhanced at hv = 47 eV, which corresponds to the Ti $3p \rightarrow 3d$ absorption edge. Feature C is due to the oxygen defects at the surface.^{6,11} The doublet structures at approximately 20 eV are the O 2s and Sr 4p core levels. The intensity of Sr 4p peaks at $\sim 23 \text{ eV}$ increases with decreasing excitation energy. This is evidently due to the excitation energy dependence of the ionization cross section of the Sr 4p electron.

Figure 2(a) shows the on- and off-resonance spectra of the valence band of $La_{1-x}Sr_xTiO_3$ measured at $h\nu = 60 \text{ eV}$. Comparing the off-resonance spectra, the intensity of the nonbonding state is lower in x = 0.01. In both on-resonance spectra, the intensities of peaks A and B are resonantly enhanced by the Ti $3p \rightarrow 3d$ excitation. The resonance effect is stronger in x = 0.01.

Figure 2(b) shows the difference spectra by subtracting the off-resonance from the on-resonance spectra. The difference spectra correspond to the Ti 3*d* PDOS in the valence band. Comparing the difference spectra, the Ti 3*d* PDOS is larger in the case of x = 0.01. This fact implies that the hybridization effect between the Ti 3*d* state and O 2*p* state becomes more extensive with La³⁺ dopant concentration, indicating that the bond length between Ti⁴⁺ and O²⁻ ions or the symmetry changes with a small amount of doping cations.

In terms of the crystal structure, it is reported that the lattice parameters increase linearly with increasing La^{3+} dopant concentration.⁵⁾ The ionic radius of La^{3+} is slightly less than that of Sr²⁺, i.e., La^{3+} : 0.123 nm and Sr²⁺: 0.125 nm for 12-fold coordination. The ionic radius of Ti³⁺, which formed for the charge compensation, is larger than that of Ti⁴⁺, i.e., Ti³⁺: 0.076 nm and Ti⁴⁺: 0.068 nm for 6-



Fig. 2. RPES spectra as a function of La doping of $La_x Sr_{1-x}TiO_3$ (x = 0.01 and 0.05). (a) On-resonance spectra measured at hv = 47 eV and off-resonance spectra measured at hv = 60 eV. (b) Difference spectra obtained by subtracting the off-resonance spectra from the on-resonance spectra.

fold coordination. The Ti³⁺ constant was approximately equal to the nominal La content for any composition based on the weight gain after the oxidation. Accordingly, the increase in lattice parameters is attributed to the increase in Ti³⁺ content of the crystal. This fact has been confirmed in the X-ray photoemission (XPS) spectra of $Y_x Ca_{1-x} TiO_3$. The band structure of $Y_x Ca_{1-x} TiO_3$ resembles with that of $La_xSr_{1-x}TiO_3$. In the XPS spectra in the Ti $2p_{3/2}$ core region, Ti^{4+} and Ti^{3+} peaks are found at ${\sim}460\,eV$ and ${\sim}462\,eV,$ respectively. $^{17)}$ The peak intensities of the Ti^{4+} and Ti^{3+} peaks vary systematically with Y^{3+} dopant concentration. This phenomenon is also expected for $La_xSr_{1-x}TiO_3$. The doped electrons enter the bottom of the empty state 3d band and the Ti 3d-originated-DOS (Ti³⁺ component) exists in the band-gap energy region.^{10–14)} Thus, the decrease in the hybridization effect between the Ti 3d and O 2p states with La doping can be explained by the decrease in the effective charges of Ti^{4+} and O^{2-} ions.

In conclusion, we measured the RPES spectra on $La_xSr_{1-x}TiO_3$ using synchrotron radiation. The RPES spectra show that the hybridization effect between the Ti 3*d* and O 2*p* states decreases with increasing La^{3+} dopant concentration. This finding indicates that the effective charge of Ti⁴⁺ and O²⁻ ions decreases with La^{3+} dopant concentration.

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